ANNEALED WAFER AND METHOD FOR PRODUCING ANNEALED WAFER

ABSTRACT

[PROBLEM]

A method for producing an annealed wafer having enhanced gettering effects for Cu is provided.

[SOLUTION]

A method for producing an annealed wafer, characterized in comprising heating a silicon substrate containing a nitrogen concentration of 5×10^{14} to $1\times10^{16}/cm^3$, a carbon concentration of 1×10^{15} to $5\times10^{16}/cm^3$, and an oxygen concentration of 6×10^{17} to $11\times10^{17}/cm^3$ at a temperature of 650 to 800 ºC for a time equal to or longer than 4 hours, and subjecting the heated substrate to argon annealing at a temperature of 1100 to 1250 ºC, wherein internal stacking fault density after annealing is equal to or higher than $5\times10^{8}/cm^3$.

[SELECTION DRAWING]

Fig. 2